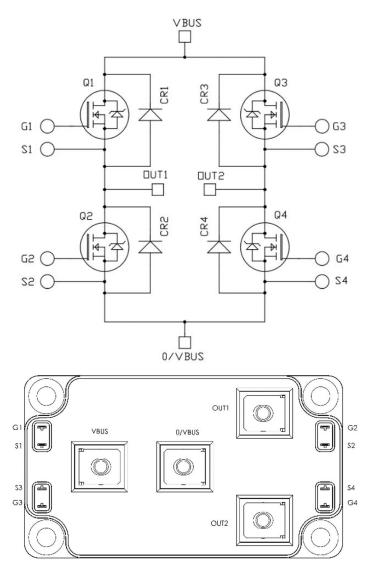
# MSCSM170HM12CAG

## **Full Bridge SiC Power Module**

## **Product Overview**

The MSCSM170HM12CAG device is a 1700 V/179 A full bridge silicon carbide (SiC) power module.



All ratings at  $T_J$  = 25 °C, unless otherwise specified.

Caution: These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

#### **Features**

The following are the key features of MSCSM170HM12CAG device:

- · SiC Power MOSFET
  - Low R<sub>DS(on)</sub>
  - High temperature performance
- · SiC Schottky Diode
  - Zero reverse recovery
  - Zero forward recovery
  - Temperature independent switching behavior
  - Positive temperature coefficient on VF
- · Kelvin source for easy drive
- · Low stray inductance
- · M5 power connectors
- Aluminum Nitride (AIN) substrate for improved thermal performance

#### **Benefits**

The following are the benefits of MSCSM170HM12CAG device:

- · High efficiency converter
- Outstanding performance at high-frequency operation
- · Stable temperature behavior
- Direct mounting to heatsink (isolated package)
- · Low junction-to-case thermal resistance
- RoHS compliant

#### **Applications**

The following are the applications of MSCSM170HM12CAG device:

- · Welding converters
- Switched mode power supplies
- · Uninterruptible power supplies
- EV motor and traction drive

## 1. Electrical Specifications

The following sections show the electrical specifications of the MSCSM170HM12CAG device.

## 1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings (per SiC MOSFET) of the MSCSM170HM12CAG device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter		Maximum Ratings	Unit	
V <sub>DSS</sub>	Drain-Source voltage		1700	V	
I <sub>D</sub>	Continuous drain current $T_C = 25 ^{\circ}\text{C}$ $T_C = 80 ^{\circ}\text{C}$		179	Α	
			142		
I <sub>DM</sub>	Pulsed drain current		360		
V <sub>GS</sub>	Gate-Source voltage		-10/23	V	
R <sub>DS(on)</sub>	Drain-Source ON resistance		15	mΩ	
P <sub>D</sub>	Power dissipation	T <sub>C</sub> = 25 °C	843	W	

The following table lists the electrical characteristics (per SiC MOSFET) of the MSCSM170HM12CAG device.

**Table 1-2. Electrical Characteristics** 

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I <sub>DSS</sub>	Zero gate voltage drain current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 1700 V		_	30	300	μΑ
R <sub>DS(on)</sub>	Drain-Source on	V <sub>GS</sub> = 20 V	T <sub>J</sub> = 25 °C	_	11.7	15	mΩ
	resistance	I <sub>D</sub> = 90 A	T <sub>J</sub> = 175 °C	_	20.8	_	
V <sub>GS(th)</sub>	Gate threshold voltage	$V_{GS} = V_{DS}; I_D = 7.5 \text{ mA}$		1.8	3.2	_	V
I <sub>GSS</sub>	Gate-Source leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V		_	_	300	nA

The following table lists the dynamic characteristics (per SiC MOSFET) of the MSCSM170HM12CAG device.

**Table 1-3. Dynamic Characteristics** 

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
C <sub>iss</sub>	Input capacitance	V <sub>GS</sub> = 0 V		_	9900	_	pF
C <sub>oss</sub>	Output capacitance	V <sub>DS</sub> = 1000 V		_	450	_	
C <sub>rss</sub>	Reverse transfer capacitance	f = 1 MHz		_	30	_	
Qg	Total gate charge	V <sub>GS</sub> = -5 V/20 V		_	534	_	nC
Q <sub>gs</sub>	Gate-source charge	V <sub>Bus</sub> = 850 V		_	147	_	
Q <sub>gd</sub>	Gate-drain charge	I <sub>D</sub> = 90 A	I <sub>D</sub> = 90 A		81	_	
T <sub>d(on)</sub>	Turn-on delay time	V <sub>GS</sub> = -5 V/20 V V <sub>Bus</sub> = 900 V		_	75	_	ns
T <sub>r</sub>	Rise time			_	75	_	
T <sub>d(off)</sub>	Turn-off delay time	I <sub>D</sub> = 150 A		_	153	_	
T <sub>f</sub>	Fall time	$T_J$ = 150 °C $R_{GON}$ = 9.4 $\Omega$ $R_{GOFF}$ = 5.4 $\Omega$			56	_	
E <sub>on</sub>	Turn-on energy	V <sub>GS</sub> = -5 V/20 V	T <sub>J</sub> = 150 °C	_	6.7	_	mJ
E <sub>off</sub>	Turn-off energy	$V_{Bus}$ = 900 V $I_{D}$ = 150 A $R_{GON}$ = 9.4 Ω $R_{GOFF}$ = 5.4 Ω	T <sub>J</sub> = 150 °C	_	3.6	_	
R <sub>Gint</sub>	Internal gate resistance			_	1.95	_	Ω
R <sub>thJC</sub>	Junction-to-case therr	mal resistance		_	_	0.178	°C/W

The following table lists the body diode ratings and characteristics (per SiC MOSFET) of the MSCSM170HM12CAG device.

Table 1-4. Body Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
$V_{SD}$	Diode forward voltage	V <sub>GS</sub> = 0 V; I <sub>SD</sub> = 90 A	_	3.7	_	V
		$V_{GS} = -5 \text{ V}; I_{SD} = 90 \text{ A}$	_	3.9	_	
t <sub>rr</sub>	Reverse recovery time	I <sub>SD</sub> = 90 A	_	27	_	ns
Q <sub>rr</sub>	Reverse recovery charge	$V_{GS} = -5 V$	_	1950	_	nC
I <sub>rr</sub>	Reverse recovery current	$V_R = 900 \text{ V}$ $di_F/dt = 3000 \text{ A/}\mu\text{s}$	_	138	_	A

## 1.2 SiC Schottky Diode Ratings and Characteristics (Per SiC Diode)

The following table lists the SiC Schottky diode ratings and characteristics of the MSCSM170HM12CAG device.

Table 1-5. SiC Schottky Diode Ratings and Characteristics (Per SiC Diode)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	Peak repetitive reverse volt	age	_	_	1700	V	
I <sub>RRM</sub>	Reverse leakage current	V <sub>R</sub> = 1700 V	T <sub>J</sub> = 25 °C	_	30	600	μA
			T <sub>J</sub> = 175 °C	_	450	_	
I <sub>F</sub>	DC forward current	_	T <sub>C</sub> = 125 °C	_	90	_	Α
V <sub>F</sub>	Diode forward voltage I <sub>F</sub> = 90 A	I <sub>F</sub> = 90 A	T <sub>J</sub> = 25 °C	_	1.5	1.8	V
			T <sub>J</sub> = 175 °C	_	2.3	_	
Q <sub>C</sub>	Total capacitive charge	V <sub>R</sub> = 900 V		_	690	_	nC
С	Total capacitance	f = 1 MHz, V <sub>R</sub> = 600 V		_	501	_	pF
	f = 1 MHz, V <sub>R</sub> = 900 V		00 V	_	414	_	
R <sub>thJC</sub>	Junction-to-case thermal re	sistance	_	_	0.197	°C/W	

## 1.3 Thermal and Package Characteristics

The following table lists the package characteristics of the MSCSM170HM12CAG device.

Table 1-6. Thermal and Package Characteristics

Symbol	Characteristic	Min	Max	Unit		
V <sub>ISOL</sub>	RMS isolation voltage, any terminal to ca	0 Hz/60 Hz	4000	_	V	
$T_J$	Operating junction temperature range			<b>-40</b>	175	°C
T <sub>JOP</sub>	Recommended junction temperature und	er switching co	onditions	-40	T <sub>Jmax</sub> –25	
T <sub>STG</sub>	Storage case temperature	-40	125			
T <sub>C</sub>	Operating case temperature	-40	125			
Torque	Mounting torque  To heatsink M6  For terminals				5	N.m
					3.5	
Wt	Package weight	_	300	g		

### 1.4 Typical SiC MOSFET Performance Curve

The following figures show the SiC MOSFET performance curves of the MSCSM170HM12CAG device.

Figure 1-1. Maximum Thermal Impedance

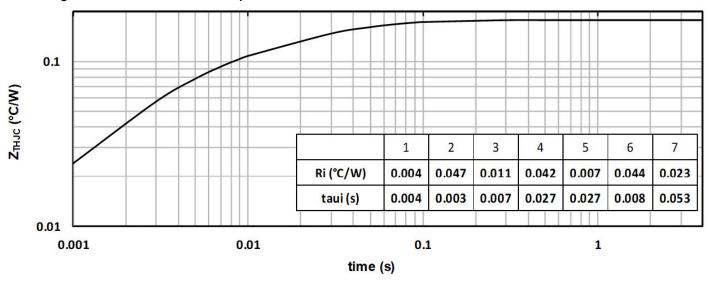


Figure 1-2. Output Characteristics,  $T_J = 25$  °C

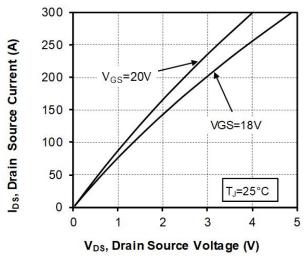


Figure 1-3. Output Characteristics, T<sub>J</sub> = 175 °C

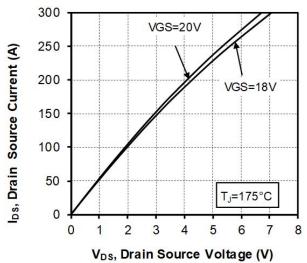


Figure 1-4. Normalized R<sub>DS(on)</sub> vs. Temperature

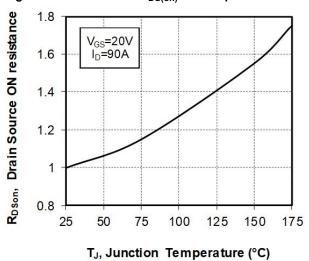


Figure 1-5. Transfer Characteristics

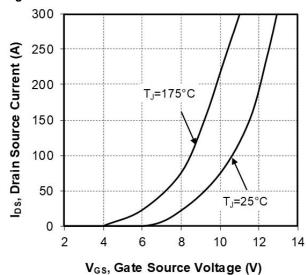


Figure 1-6. Switching Energy vs. Rg

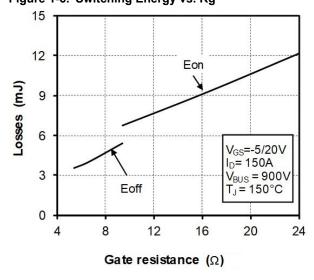
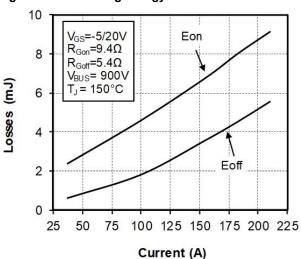
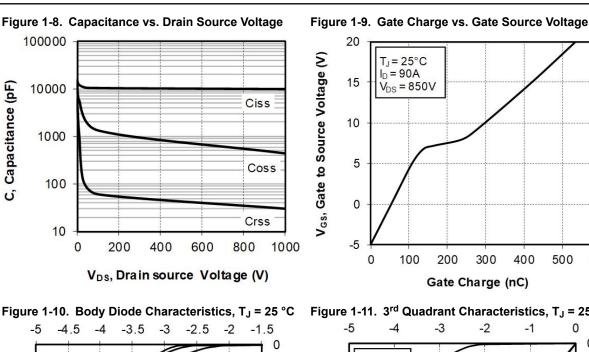


Figure 1-7. Switching Energy vs. Current





V<sub>GS</sub>, Gate to Source Voltage (V)  $T_J = 25^{\circ}C$  $I_D = 90A$ 15  $V_{DS} = 850V$ 10 5 0 -5 0 100 200 300 400 500 600 Gate Charge (nC)

los, Drain source current (A) V<sub>GS</sub>=-5V -50 V<sub>GS</sub>=0V -100 -150 V<sub>GS</sub>=-2V -200 -250T<sub>J</sub>=25°C -300 V<sub>DS</sub>, Drain source voltage (V)

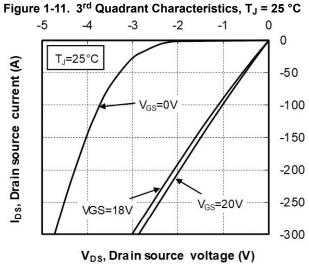
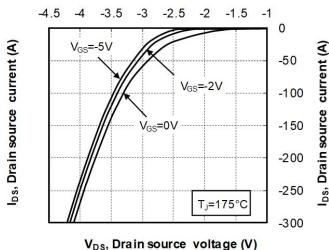
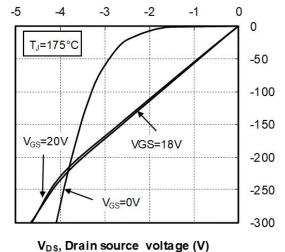


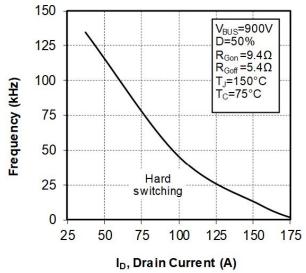
Figure 1-12. Body Diode Characteristics, T<sub>J</sub> = 175 °C Figure 1-13. 3<sup>rd</sup> Quadrant Characteristics, T<sub>J</sub> = 175 °C





**Datasheet** DS00003995A-page 8

Figure 1-14. Operating Frequency vs. Drain Current



### 1.5 Typical SiC Diode Performance Curve

The following figures show the SiC diode performance curves of the MSCSM170HM12CAG device.

Figure 1-15. Maximum Thermal Impedance

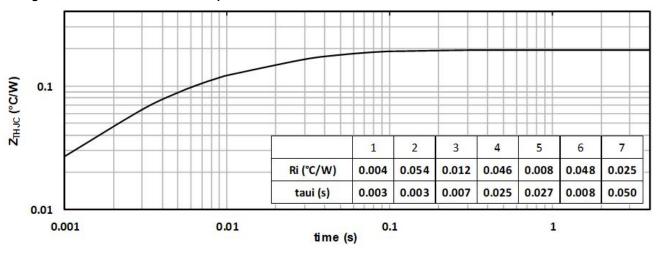


Figure 1-16. Forward Characteristics

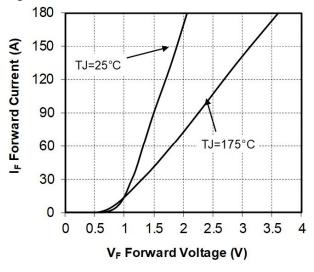
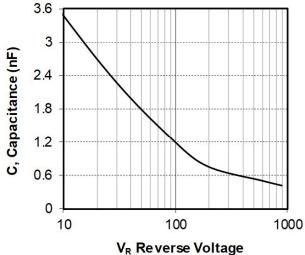


Figure 1-17. Capacitance vs. Reverse Voltage



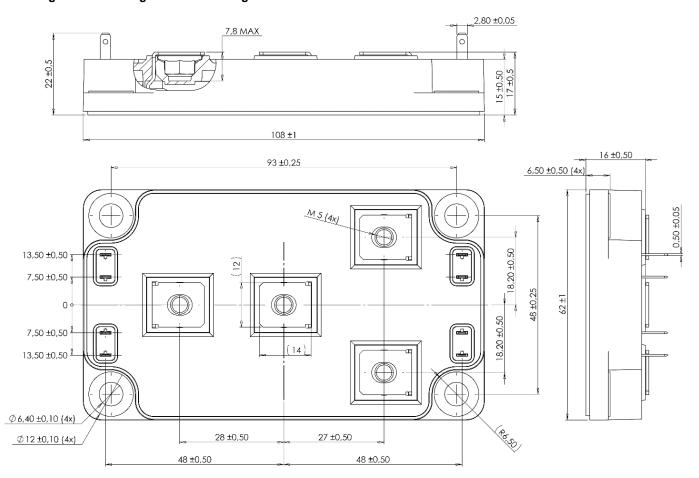
## 2. Package Specifications

The following section shows the package specification of the MSCSM170HM12CAG device.

## 2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM170HM12CAG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



Note: See application note APT0601—Mounting Instructions for SP6 Power Modules for more information.

# 3. Revision History

Revision	Date	Description
Α	05/2021	This is the first publication of this document.

## The Microchip Website

Microchip provides online support via our website at <a href="www.microchip.com/">www.microchip.com/</a>. This website is used to make files and information easily available to customers. Some of the content available includes:

- Product Support Data sheets and errata, application notes and sample programs, design resources, user's
  guides and hardware support documents, latest software releases and archived software
- General Technical Support Frequently Asked Questions (FAQs), technical support requests, online discussion groups, Microchip design partner program member listing
- Business of Microchip Product selector and ordering guides, latest Microchip press releases, listing of seminars and events, listings of Microchip sales offices, distributors and factory representatives

## **Product Change Notification Service**

Microchip's product change notification service helps keep customers current on Microchip products. Subscribers will receive email notification whenever there are changes, updates, revisions or errata related to a specified product family or development tool of interest.

To register, go to www.microchip.com/pcn and follow the registration instructions.

## **Customer Support**

Users of Microchip products can receive assistance through several channels:

- · Distributor or Representative
- · Local Sales Office
- Embedded Solutions Engineer (ESE)
- Technical Support

Customers should contact their distributor, representative or ESE for support. Local sales offices are also available to help customers. A listing of sales offices and locations is included in this document.

Technical support is available through the website at: www.microchip.com/support

## Microchip Devices Code Protection Feature

Note the following details of the code protection feature on Microchip devices:

- · Microchip products meet the specifications contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is secure when used in the intended manner and under normal
  conditions.
- There are dishonest and possibly illegal methods being used in attempts to breach the code protection features
  of the Microchip devices. We believe that these methods require using the Microchip products in a manner
  outside the operating specifications contained in Microchip's Data Sheets. Attempts to breach these code
  protection features, most likely, cannot be accomplished without violating Microchip's intellectual property rights.
- Microchip is willing to work with any customer who is concerned about the integrity of its code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of its code. Code
  protection does not mean that we are guaranteeing the product is "unbreakable." Code protection is constantly
  evolving. We at Microchip are committed to continuously improving the code protection features of our products.
  Attempts to break Microchip's code protection feature may be a violation of the Digital Millennium Copyright Act.
  If such acts allow unauthorized access to your software or other copyrighted work, you may have a right to sue
  for relief under that Act.

## **Legal Notice**

Information contained in this publication is provided for the sole purpose of designing with and using Microchip products. Information regarding device applications and the like is provided only for your convenience and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications.

THIS INFORMATION IS PROVIDED BY MICROCHIP "AS IS". MICROCHIP MAKES NO REPRESENTATIONS OR WARRANTIES OF ANY KIND WHETHER EXPRESS OR IMPLIED, WRITTEN OR ORAL, STATUTORY OR OTHERWISE, RELATED TO THE INFORMATION INCLUDING BUT NOT LIMITED TO ANY IMPLIED WARRANTIES OF NON-INFRINGEMENT, MERCHANTABILITY, AND FITNESS FOR A PARTICULAR PURPOSE OR WARRANTIES RELATED TO ITS CONDITION, QUALITY, OR PERFORMANCE.

IN NO EVENT WILL MICROCHIP BE LIABLE FOR ANY INDIRECT, SPECIAL, PUNITIVE, INCIDENTAL OR CONSEQUENTIAL LOSS, DAMAGE, COST OR EXPENSE OF ANY KIND WHATSOEVER RELATED TO THE INFORMATION OR ITS USE, HOWEVER CAUSED, EVEN IF MICROCHIP HAS BEEN ADVISED OF THE POSSIBILITY OR THE DAMAGES ARE FORESEEABLE. TO THE FULLEST EXTENT ALLOWED BY LAW, MICROCHIP'S TOTAL LIABILITY ON ALL CLAIMS IN ANY WAY RELATED TO THE INFORMATION OR ITS USE WILL NOT EXCEED THE AMOUNT OF FEES, IF ANY, THAT YOU HAVE PAID DIRECTLY TO MICROCHIP FOR THE INFORMATION. Use of Microchip devices in life support and/or safety applications is entirely at the buyer's risk, and the buyer agrees to defend, indemnify and hold harmless Microchip from any and all damages, claims, suits, or expenses resulting from such use. No licenses are conveyed, implicitly or otherwise, under any Microchip intellectual property rights unless otherwise stated.

#### **Trademarks**

The Microchip name and logo, the Microchip logo, Adaptec, AnyRate, AVR, AVR logo, AVR Freaks, BesTime, BitCloud, chipKIT, chipKIT logo, CryptoMemory, CryptoRF, dsPIC, FlashFlex, flexPWR, HELDO, IGLOO, JukeBlox, KeeLoq, Kleer, LANCheck, LinkMD, maXStylus, maXTouch, MediaLB, megaAVR, Microsemi, Microsemi logo, MOST, MOST logo, MPLAB, OptoLyzer, PackeTime, PIC, picoPower, PICSTART, PIC32 logo, PolarFire, Prochip Designer, QTouch, SAM-BA, SenGenuity, SpyNIC, SST, SST Logo, SuperFlash, Symmetricom, SyncServer, Tachyon, TimeSource, tinyAVR, UNI/O, Vectron, and XMEGA are registered trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

AgileSwitch, APT, ClockWorks, The Embedded Control Solutions Company, EtherSynch, FlashTec, Hyper Speed Control, HyperLight Load, IntelliMOS, Libero, motorBench, mTouch, Powermite 3, Precision Edge, ProASIC, ProASIC Plus, ProASIC Plus logo, Quiet-Wire, SmartFusion, SyncWorld, Temux, TimeCesium, TimeHub, TimePictra, TimeProvider, WinPath, and ZL are registered trademarks of Microchip Technology Incorporated in the U.S.A.

Adjacent Key Suppression, AKS, Analog-for-the-Digital Age, Any Capacitor, Anyln, AnyOut, Augmented Switching, BlueSky, BodyCom, CodeGuard, CryptoAuthentication, CryptoAutomotive, CryptoCompanion, CryptoController, dsPICDEM, dsPICDEM.net, Dynamic Average Matching, DAM, ECAN, Espresso T1S, EtherGREEN, IdealBridge, In-Circuit Serial Programming, ICSP, INICnet, Intelligent Paralleling, Inter-Chip Connectivity, JitterBlocker, maxCrypto, maxView, memBrain, Mindi, MiWi, MPASM, MPF, MPLAB Certified logo, MPLIB, MPLINK, MultiTRAK, NetDetach, Omniscient Code Generation, PICDEM, PICDEM.net, PICkit, PICtail, PowerSmart, PureSilicon, QMatrix, REAL ICE, Ripple Blocker, RTAX, RTG4, SAM-ICE, Serial Quad I/O, simpleMAP, SimpliPHY, SmartBuffer, SMART-I.S., storClad, SQI, SuperSwitcher, SuperSwitcher II, Switchtec, SynchroPHY, Total Endurance, TSHARC, USBCheck, VariSense, VectorBlox, VeriPHY, ViewSpan, WiperLock, XpressConnect, and ZENA are trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

SQTP is a service mark of Microchip Technology Incorporated in the U.S.A.

The Adaptec logo, Frequency on Demand, Silicon Storage Technology, and Symmcom are registered trademarks of Microchip Technology Inc. in other countries.

GestIC is a registered trademark of Microchip Technology Germany II GmbH & Co. KG, a subsidiary of Microchip Technology Inc., in other countries.

All other trademarks mentioned herein are property of their respective companies.

© 2021, Microchip Technology Incorporated, Printed in the U.S.A., All Rights Reserved.

ISBN: 978-1-5224-8196-6

# **Quality Management System**

For information regarding Microchip's Quality Management Systems, please visit www.microchip.com/quality.



# **Worldwide Sales and Service**

AMERICAS	ASIA/PACIFIC	ASIA/PACIFIC	EUROPE
Corporate Office	Australia - Sydney	India - Bangalore	Austria - Wels
2355 West Chandler Blvd.	Tel: 61-2-9868-6733	Tel: 91-80-3090-4444	Tel: 43-7242-2244-39
Chandler, AZ 85224-6199	China - Beijing	India - New Delhi	Fax: 43-7242-2244-393
Tel: 480-792-7200	Tel: 86-10-8569-7000	Tel: 91-11-4160-8631	Denmark - Copenhagen
Fax: 480-792-7277	China - Chengdu	India - Pune	Tel: 45-4485-5910
Technical Support:	Tel: 86-28-8665-5511	Tel: 91-20-4121-0141	Fax: 45-4485-2829
www.microchip.com/support	China - Chongqing	Japan - Osaka	Finland - Espoo
Web Address:	Tel: 86-23-8980-9588	Tel: 81-6-6152-7160	Tel: 358-9-4520-820
www.microchip.com	China - Dongguan	Japan - Tokyo	France - Paris
Atlanta	Tel: 86-769-8702-9880	Tel: 81-3-6880- 3770	Tel: 33-1-69-53-63-20
Duluth, GA	China - Guangzhou	Korea - Daegu	Fax: 33-1-69-30-90-79
Tel: 678-957-9614	Tel: 86-20-8755-8029	Tel: 82-53-744-4301	Germany - Garching
Fax: 678-957-1455	China - Hangzhou	Korea - Seoul	Tel: 49-8931-9700
Austin, TX	Tel: 86-571-8792-8115	Tel: 82-2-554-7200	Germany - Haan
Tel: 512-257-3370	China - Hong Kong SAR	Malaysia - Kuala Lumpur	Tel: 49-2129-3766400
Boston	Tel: 852-2943-5100	Tel: 60-3-7651-7906	Germany - Heilbronn
Westborough, MA	China - Nanjing	Malaysia - Penang	Tel: 49-7131-72400
Tel: 774-760-0087	Tel: 86-25-8473-2460	Tel: 60-4-227-8870	Germany - Karlsruhe
Fax: 774-760-0088	China - Qingdao	Philippines - Manila	Tel: 49-721-625370
Chicago	Tel: 86-532-8502-7355	Tel: 63-2-634-9065	Germany - Munich
Itasca, IL	China - Shanghai	Singapore	Tel: 49-89-627-144-0
Tel: 630-285-0071	Tel: 86-21-3326-8000	Tel: 65-6334-8870	Fax: 49-89-627-144-44
Fax: 630-285-0075	China - Shenyang	Taiwan - Hsin Chu	Germany - Rosenheim
Dallas	Tel: 86-24-2334-2829	Tel: 886-3-577-8366	Tel: 49-8031-354-560
Addison, TX	China - Shenzhen	Taiwan - Kaohsiung	Israel - Ra'anana
Tel: 972-818-7423	Tel: 86-755-8864-2200	Tel: 886-7-213-7830	Tel: 972-9-744-7705
Fax: 972-818-2924	China - Suzhou	Taiwan - Taipei	Italy - Milan
Detroit	Tel: 86-186-6233-1526	Tel: 886-2-2508-8600	Tel: 39-0331-742611
Novi, MI	China - Wuhan	Thailand - Bangkok	Fax: 39-0331-466781
Tel: 248-848-4000	Tel: 86-27-5980-5300	Tel: 66-2-694-1351	Italy - Padova
Houston, TX	China - Xian	Vietnam - Ho Chi Minh	Tel: 39-049-7625286
Tel: 281-894-5983	Tel: 86-29-8833-7252	Tel: 84-28-5448-2100	Netherlands - Drunen
Indianapolis	China - Xiamen		Tel: 31-416-690399
Noblesville, IN	Tel: 86-592-2388138		Fax: 31-416-690340
Tel: 317-773-8323	China - Zhuhai		Norway - Trondheim
Fax: 317-773-5453	Tel: 86-756-3210040		Tel: 47-72884388
Tel: 317-536-2380	15 55 155 52 155 15		Poland - Warsaw
Los Angeles			Tel: 48-22-3325737
Mission Viejo, CA			Romania - Bucharest
Tel: 949-462-9523			Tel: 40-21-407-87-50
Fax: 949-462-9608			Spain - Madrid
Tel: 951-273-7800			Tel: 34-91-708-08-90
Raleigh, NC			Fax: 34-91-708-08-91
Tel: 919-844-7510			Sweden - Gothenberg
New York, NY			Tel: 46-31-704-60-40
Tel: 631-435-6000			Sweden - Stockholm
San Jose, CA			Tel: 46-8-5090-4654
Tel: 408-735-9110			UK - Wokingham
Tel: 408-436-4270			Tel: 44-118-921-5800
Canada - Toronto			Fax: 44-118-921-5820
Tel: 905-695-1980			1 da. 77-110-321-3020
Fax: 905-695-2078			
I ax. 300-030-20/0			